

# **METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE WITH CONTACT BODY EXTENDED IN DIRECTION OF BIT LINE**

5

## **ABSTRACT OF THE DISCLOSURE**

Methods for manufacturing semiconductor devices with contact bodies extended in a direction of a bit line to increase the contact area between a contact body and a storage electrode is provided. In one aspect a method includes forming gate lines on a semiconductor substrate, forming a first  
10 insulating layer to cover the gate lines, forming first contact pads and second contact pads, which are electrically connected to the semiconductor substrate between the gate lines, by penetrating the first insulating layer. Further, a second insulating layer is formed to cover the first contact pads and the second contact pads, and bit lines are formed across over the gate lines and are electrically  
15 connected to the second contact pads by penetrating the second insulating layer. In addition, a third insulating layer is formed to cover the bit lines and is selectively etched to form a band-type opening that crosses the bit lines and exposes the first contact pads.